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Docket: 0756-711

Date: March 17, 1992

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Honorable Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Sir:

Transmitted herewith for filing is the Rule 53(b) Patent  
Application of:

*1-00 et al*  
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Hongyong ZHANG  
Naoto KUSUMOTO  
Yasuhiko TAKEMURA

For: SEMICONDUCTOR MATERIAL AND METHOD FOR  
FORMING THE SAME AND THIN FILM TRANSISTOR

Enclosed are:

[ X ] 33 pages of specification and claims  
[ X ] 6 sheets of drawings ( ) formal (X) informal

[ X ] Priority is claimed based on foreign application(s)  
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Respectfully submitted,

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CITIZENSHIP: Japan (all)  
TITLE: SEMICONDUCTOR MATERIAL AND METHOD FOR FORMING  
THE SAME AND THIN FILM TRANSISTOR

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PRIORITY: Country: Federal Republic of Germany  
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